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FEATURES

- Low power at high voltage (18 V): 725 μ A maximum
- Low offset voltage
 - 150 μ V maximum at $V_{SY}/2$
 - 300 μ V maximum over entire common-mode range
- Low input bias current: 15 pA maximum
- Gain bandwidth product: 4 MHz typical at $A_v = 100$
- Unity-gain crossover: 4 MHz typical
- 3 dB closed-loop bandwidth: 2.1 MHz typical
- Single-supply operation: 3 V to 18 V
- Dual-supply operation: ± 1.5 V to ± 9 V
- Unity-gain stable

APPLICATIONS

- Current shunt monitors
- Active filters
- Portable medical equipment
- Buffer/level shifting
- High impedance sensor interfaces
- Battery powered instrumentation

GENERAL DESCRIPTION

The ADA4661-2 is a dual, precision, rail-to-rail input/output amplifier optimized for low power, high bandwidth, and wide operating supply voltage range applications.

The ADA4661-2 performance is guaranteed at 3.0 V, 10 V, and 18 V power supply voltages. It is an excellent selection for applications that use single-ended supplies of 3.3 V, 5 V, 10 V, 12 V and 15 V, and dual supplies of ± 2.5 V, ± 3.3 V, and ± 5 V. It uses the Analog Devices, Inc., patented DigiTrim[®] trimming technique, which achieves low offset voltage. Additionally, the unique design architecture of the ADA4661-2 allows it to have excellent power supply rejection, common-mode rejection, and offset voltage when operating in the common-mode voltage range of $-V_{SY} + 1.5$ V to $+V_{SY} - 1.5$ V.

The ADA4661-2 is specified over the extended industrial temperature range (-40°C to $+125^{\circ}\text{C}$) and is available in 8-lead MSOP and 8-lead LFCSP (3 mm \times 3 mm) packages.

PIN CONNECTION DIAGRAMS

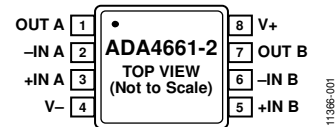
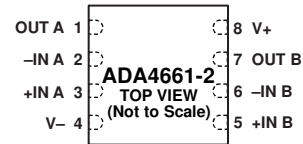


Figure 1. 8-Lead MSOP



- NOTES
1. CONNECT THE EXPOSED PAD TO V- OR LEAVE IT UNCONNECTED.

Figure 2. 8-Lead LFCSP

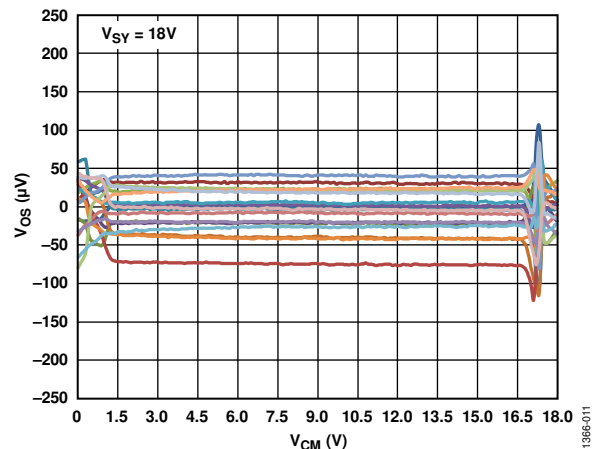


Figure 3. Input Offset Voltage vs. Common-Mode Voltage

Table 1. Precision Low Power Op Amps (<1 mA)

Supply Voltage	5 V	12 V to 16 V	30 V
Single	ADA4505-1 AD8500	OP196	OP777
Dual	ADA4505-2 AD8502 AD8506	AD8657 OP296 ADA4661-2 ADA4666-2	ADA4096-2 OP727 AD8682 AD8622
Quad	ADA4505-4 AD8504 AD8508	AD8659 OP496	ADA4096-4 OP747 AD8684 AD8624

ADA4661-2* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

DOCUMENTATION

Application Notes

- AN-763: Dual Universal Precision Op Amp Evaluation Board

Data Sheet

- ADA4661-2: 18 V, Precision, 725 μ A, 4 MHz CMOS RRIO Operational Amplifier Data Sheet

Technical Books

- Practical Design Techniques for Sensor Signal Conditioning, 1999

TOOLS AND SIMULATIONS

- Amplifiers & Linear Tools
- Analog Filter Wizard
- Analog Photodiode Wizard
- ADA4661 SPICE Macro Model

REFERENCE DESIGNS

- CN0398

REFERENCE MATERIALS

Technical Articles

- MS-2212: The Maximum Supply Current That Wasn't

Tutorials

- MT-035: Op Amp Inputs, Outputs, Single-Supply, and Rail-to-Rail Issues
- MT-047: Op Amp Noise

DESIGN RESOURCES

- ADA4661-2 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all ADA4661-2 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

Submit feedback for this data sheet.

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REVISION HISTORY

7/13—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—18 V OPERATION

$V_{SY} = 18\text{ V}$, $V_{CM} = V_{SY}/2\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise specified.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = 1.5\text{ V to }16.5\text{ V}$		30	150	μV
		$V_{CM} = 1.5\text{ V to }16.5\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			150	μV
		$V_{CM} = 0\text{ V to }18\text{ V}$			500	μV
		$V_{CM} = 0\text{ V to }18\text{ V}$			300	μV
		$V_{CM} = 0\text{ V to }18\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			600	μV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.6	3.1	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	I_B	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		0.5	15	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			100	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			900	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			11	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			30	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			300	pA
Input Voltage Range			0		18	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 1.5\text{ V to }16.5\text{ V}$	115	135		dB
		$V_{CM} = 1.5\text{ V to }16.5\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	110			dB
		$V_{CM} = 0\text{ V to }18\text{ V}$	100	118		dB
		$V_{CM} = 0\text{ V to }18\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	91			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 100\text{ k}\Omega$, $V_{OUT} = 0.5\text{ V to }17.5\text{ V}$	120	147		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	120			dB
Input Resistance						
Differential Mode	R_{INDM}			>10		$\text{G}\Omega$
Common Mode	R_{INCM}			>10		$\text{G}\Omega$
Input Capacitance						
Differential Mode	C_{INDM}			8.5		pF
Common Mode	C_{INCM}			3		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 10\text{ k}\Omega$ to V_{CM}	17.95	17.97		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	17.94			V
		$R_L = 1\text{ k}\Omega$ to V_{CM}	17.6	17.79		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	17.58			V
Output Voltage Low	V_{OL}	$R_L = 10\text{ k}\Omega$ to V_{CM}		14	25	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			40	mV
		$R_L = 1\text{ k}\Omega$ to V_{CM}		120	200	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			300	mV
Continuous Output Current	I_{OUT}	Dropout voltage = 1 V		40		mA
Short-Circuit Current	I_{SC}	Pulse width = 10 ms; refer to the Maximum Power Dissipation section		± 220		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 100\text{ kHz}$, $A_v = 1$		0.2		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 3.0\text{ V to }18\text{ V}$	120	145		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	120			dB
Supply Current per Amplifier	I_{SY}	$I_{OUT} = 0\text{ mA}$		630	725	μA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			975	μA

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_S = 1\text{ k}\Omega, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 1$		2		V/ μ s
Gain Bandwidth Product	GBP	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 100$		4		MHz
Unity-Gain Crossover	UGC	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_{VO} = 1$		4		MHz
-3 dB Closed-Loop Bandwidth	$f_{-3\text{ dB}}$	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 1$		2.1		MHz
Phase Margin	Φ_M	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_{VO} = 1$		60		Degrees
Settling Time to 0.1%	t_s	$V_{IN} = 1\text{ V step}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}$		1.3		μ s
Channel Separation	CS	$V_{IN} = 17.9\text{ V p-p}, f = 10\text{ kHz}, R_L = 10\text{ k}\Omega$		80		dB
EMI Rejection Ratio of +IN x	EMIRR	$V_{IN} = 100\text{ mV peak (200 mV p-p)}$				
f = 400 MHz				34		dB
f = 900 MHz				42		dB
f = 1800 MHz				50		dB
f = 2400 MHz				60		dB
NOISE PERFORMANCE						
Total Harmonic Distortion Plus Noise	THD + N	$A_V = 1, V_{IN} = 5.4\text{ V rms at } 1\text{ kHz}$				
Bandwidth = 80 kHz				0.0004		%
Bandwidth = 500 kHz				0.0008		%
Peak-to-Peak Noise	$e_n\text{ p-p}$	f = 0.1 Hz to 10 Hz		3		μ V p-p
Voltage Noise Density	e_n	f = 1 kHz		18		nV/ $\sqrt{\text{Hz}}$
		f = 10 kHz		14		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	f = 1 kHz		360		fA/ $\sqrt{\text{Hz}}$

ELECTRICAL CHARACTERISTICS—10 V OPERATION

$V_{SY} = 10\text{ V}$, $V_{CM} = V_{SY}/2\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise specified.

Table 3.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = 1.5\text{ V to }8.5\text{ V}$		30	150	μV
		$V_{CM} = 1.5\text{ V to }8.5\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			150	μV
		$V_{CM} = 0\text{ V to }10\text{ V}$			450	μV
		$V_{CM} = 0\text{ V to }10\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			300	μV
					600	μV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.6	3.1	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	I_B	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		0.25	15	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			80	pA
					750	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			11	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			30	pA
					270	pA
Input Voltage Range			0		10	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 1.5\text{ V to }8.5\text{ V}$	115	140		dB
		$V_{CM} = 1.5\text{ V to }8.5\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	115			dB
		$V_{CM} = 0\text{ V to }10\text{ V}$	95	114		dB
		$V_{CM} = 0\text{ V to }10\text{ V}; -40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	86			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 100\text{ k}\Omega$, $V_{OUT} = 0.5\text{ V to }9.5\text{ V}$	120	145		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	120			dB
Input Resistance						
Differential Mode	R_{INDM}			>10		$\text{G}\Omega$
Common Mode	R_{INCM}			>10		$\text{G}\Omega$
Input Capacitance						
Differential Mode	C_{INDM}			8.5		pF
Common Mode	C_{INCM}			3		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 10\text{ k}\Omega$ to V_{CM}	9.96	9.98		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	9.96			V
		$R_L = 1\text{ k}\Omega$ to V_{CM}	9.7	9.88		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	9.7			V
Output Voltage Low	V_{OL}	$R_L = 10\text{ k}\Omega$ to V_{CM}		10	15	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			30	mV
		$R_L = 1\text{ k}\Omega$ to V_{CM}		77	110	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			200	mV
Continuous Output Current	I_{OUT}	Dropout voltage = 1 V		40		mA
Short-Circuit Current	I_{SC}	Pulse width = 10 ms; refer to the Maximum Power Dissipation section		± 220		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 100\text{ kHz}$, $A_V = 1$		0.2		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 3.0\text{ V to }18\text{ V}$	120	145		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	120			dB
Supply Current per Amplifier	I_{SY}	$I_{OUT} = 0\text{ mA}$		620	725	μA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			975	μA

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_S = 1\text{ k}\Omega, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 1$		1.8		V/ μ s
Gain Bandwidth Product	GBP	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 100$		4		MHz
Unity-Gain Crossover	UGC	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_{VO} = 1$		4		MHz
-3 dB Closed-Loop Bandwidth	$f_{-3\text{ dB}}$	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_V = 1$		2.1		MHz
Phase Margin	Φ_M	$V_{IN} = 10\text{ mV p-p}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}, A_{VO} = 1$		60		Degrees
Settling Time to 0.1%	t_s	$V_{IN} = 1\text{ V step}, R_L = 10\text{ k}\Omega, C_L = 10\text{ pF}$		1.3		μ s
Channel Separation	CS	$V_{IN} = 9.9\text{ V p-p}, f = 10\text{ kHz}, R_L = 10\text{ k}\Omega$		85		dB
EMI Rejection Ratio of +IN x	EMIRR	$V_{IN} = 100\text{ mV peak (200 mV p-p)}$				
f = 400 MHz				34		dB
f = 900 MHz				42		dB
f = 1800 MHz				50		dB
f = 2400 MHz				60		dB
NOISE PERFORMANCE						
Total Harmonic Distortion Plus Noise	THD + N	$A_V = 1, V_{IN} = 2.2\text{ V rms at } 1\text{ kHz}$				
Bandwidth = 80 kHz				0.0004		%
Bandwidth = 500 kHz				0.0008		%
Peak-to-Peak Noise	$e_n\text{ p-p}$	f = 0.1 Hz to 10 Hz		3		μ V p-p
Voltage Noise Density	e_n	f = 1 kHz		18		nV/ $\sqrt{\text{Hz}}$
		f = 10 kHz		14		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	f = 1 kHz		360		fA/ $\sqrt{\text{Hz}}$

ELECTRICAL CHARACTERISTICS—3.0 V OPERATION

$V_{SY} = 3.0\text{ V}$, $V_{CM} = V_{SY}/2$, $T_A = 25^\circ\text{C}$, unless otherwise specified.

Table 4.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = V_{SY}/2$; $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		30	150	μV
		$V_{CM} = 0\text{ V to }3.0\text{ V}$			450	μV
		$V_{CM} = 0\text{ V to }3.0\text{ V}$; $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			300	μV
					600	μV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.6	3.1	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	I_B	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$		0.15	8	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			45	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			650	pA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			11	pA
					30	pA
					270	pA
Input Voltage Range			0		3	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0\text{ V to }3.0\text{ V}$	85	100		dB
		$V_{CM} = 0\text{ V to }3.0\text{ V}$; $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	75			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 100\text{ k}\Omega$, $V_{OUT} = 0.5\text{ V to }2.5\text{ V}$	105	130		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	105			dB
Input Resistance						
Differential Mode	R_{INDM}			>10		$\text{G}\Omega$
Common Mode	R_{INCM}			>10		$\text{G}\Omega$
Input Capacitance						
Differential Mode	C_{INDM}			8.5		pF
Common Mode	C_{INCM}			3		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 10\text{ k}\Omega$ to V_{CM}	2.98	2.99		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	2.98			V
		$R_L = 1\text{ k}\Omega$ to V_{CM}	2.9	2.96		V
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	2.9			V
Output Voltage Low	V_{OL}	$R_L = 10\text{ k}\Omega$ to V_{CM}		4	8	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			15	mV
		$R_L = 1\text{ k}\Omega$ to V_{CM}		25	40	mV
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			65	mV
Continuous Output Current	I_{OUT}	Dropout voltage = 1 V		30		mA
Short-Circuit Current	I_{SC}	Pulse width = 10 ms; refer to the Maximum Power Dissipation section		± 220		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 100\text{ kHz}$, $A_V = 1$		0.2		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{SY} = 3.0\text{ V to }18\text{ V}$	120	145		dB
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	120			dB
Supply Current per Amplifier	I_{SY}	$I_{OUT} = 0\text{ mA}$		615	725	μA
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			975	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_S = 1\text{ k}\Omega$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, $A_V = 1$		1.7		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP	$V_{IN} = 10\text{ mV p-p}$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, $A_V = 100$		4		MHz
Unity-Gain Crossover	UGC	$V_{IN} = 10\text{ mV p-p}$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, $A_{VO} = 1$		4		MHz
-3 dB Closed-Loop Bandwidth	$f_{-3\text{dB}}$	$V_{IN} = 10\text{ mV p-p}$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, $A_V = 1$		1.7		MHz
Phase Margin	Φ_M	$V_{IN} = 10\text{ mV p-p}$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$, $A_{VO} = 1$		60		Degrees
Settling Time to 0.1%	t_S	$V_{IN} = 1\text{ V step}$, $R_L = 10\text{ k}\Omega$, $C_L = 10\text{ pF}$		1.3		μs
Channel Separation	CS	$V_{IN} = 2.9\text{ V p-p}$, $f = 10\text{ kHz}$, $R_L = 10\text{ k}\Omega$		90		dB

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
EMI Rejection Ratio of +IN x f = 400 MHz f = 900 MHz f = 1800 MHz f = 2400 MHz	EMIRR	$V_{IN} = 100 \text{ mV peak (200 mV p-p)}$		34 42 50 60		dB dB dB dB
NOISE PERFORMANCE						
Total Harmonic Distortion Plus Noise Bandwidth = 80 kHz Bandwidth = 500 kHz	THD + N	$A_V = 1, V_{IN} = 0.44 \text{ V rms at 1 kHz}$		0.002 0.003		% %
Peak-to-Peak Noise	$e_n \text{ p-p}$	f = 0.1 Hz to 10 Hz		3		$\mu\text{V p-p}$
Voltage Noise Density	e_n	f = 1 kHz f = 10 kHz		18 14		nV/ $\sqrt{\text{Hz}}$ nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	f = 1 kHz		360		fA/ $\sqrt{\text{Hz}}$

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
Supply Voltage	20.5 V
Input Voltage	(V ₋) – 300 mV to (V ₊) + 300 mV
Input Current ¹	±10 mA
Differential Input Voltage	Limited by maximum input current
Output Short-Circuit Duration to GND	Refer to the Maximum Power Dissipation section
Temperature Range	
Storage	–65°C to +150°C
Operating	–40°C to +125°C
Junction	–65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C
ESD	
Human Body Model ²	4 kV
Machine Model ³	400 V
Field-Induced Charged-Device Model (FICDM) ⁴	1.25 kV

¹ The input pins have clamp diodes to the power supply pins and to each other. Limit the input current to 10 mA or less when input signals exceed the power supply rail by 0.3 V.

² Applicable standard: MIL-STD-883, Method 3015.7.

³ Applicable standard: JESD22-A115-A (ESD machine model standard of JEDEC).

⁴ Applicable Standard JESD22-C101C (ESD FICDM standard of JEDEC).

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages using a standard 4-layer JEDEC board. The exposed pad of the LFCSP package is soldered to the board.

Table 6. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead MSOP	142	45	°C/W
8-Lead LFCSP	83.5	48.5 ¹	°C/W

¹ θ_{JC} is measured on the top surface of the package.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

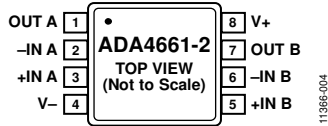
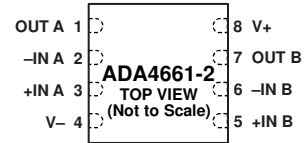


Figure 4. Pin Configuration, 8-Lead MSOP



NOTES
 1. CONNECT THE EXPOSED PAD TO V- OR LEAVE IT UNCONNECTED.

Figure 5. Pin Configuration, 8-Lead LFCSP

Table 7. Pin Function Descriptions

Pin No. ¹		Mnemonic	Description
8-Lead MSOP	8-Lead LFCSP		
1	1	OUT A	Output, Channel A.
2	2	-IN A	Negative Input, Channel A.
3	3	+IN A	Positive Input, Channel A.
4	4	V-	Negative Supply Voltage.
5	5	+IN B	Positive Input, Channel B.
6	6	-IN B	Negative Input, Channel B.
7	7	OUT B	Output, Channel B.
8	8	V+	Positive Supply Voltage.
N/A	9 ²	EPAD	Exposed Pad. For the 8-lead LFCSP only, connect the exposed pad to V- or leave it unconnected.

¹ N/A means not applicable.

² The exposed pad is not shown in the pin configuration diagram, Figure 5.

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, unless otherwise noted.

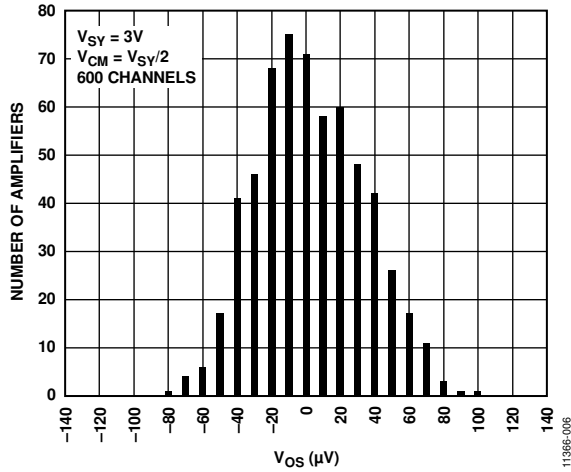


Figure 6. Input Offset Voltage Distribution

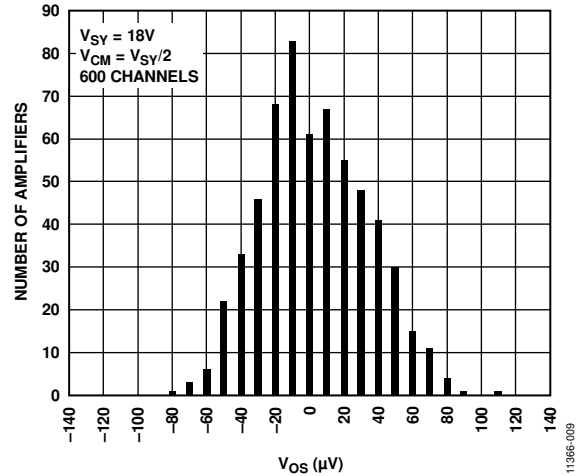


Figure 9. Input Offset Voltage Distribution

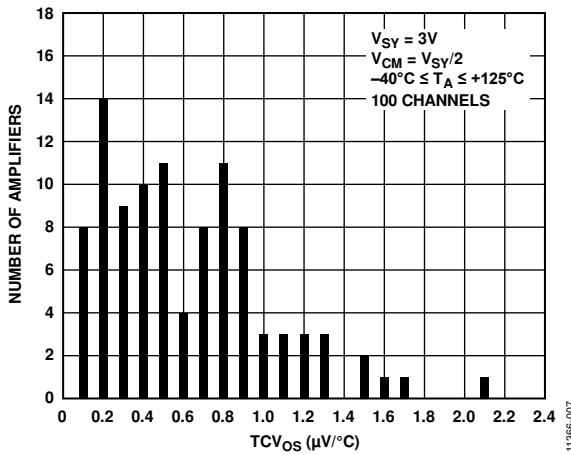


Figure 7. Input Offset Voltage Drift Distribution

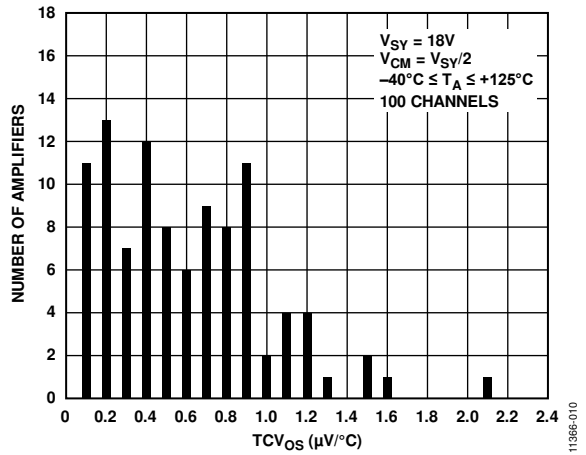


Figure 10. Input Offset Voltage Drift Distribution

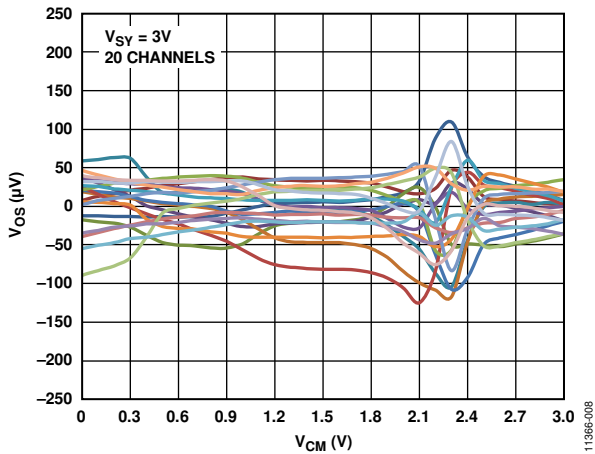


Figure 8. Input Offset Voltage vs. Common-Mode Voltage

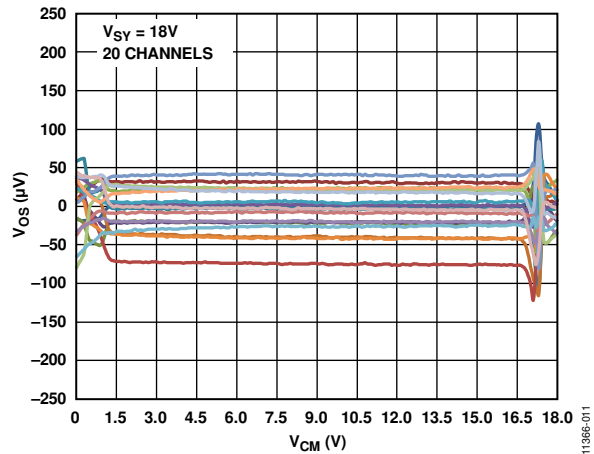


Figure 11. Input Offset Voltage vs. Common-Mode Voltage

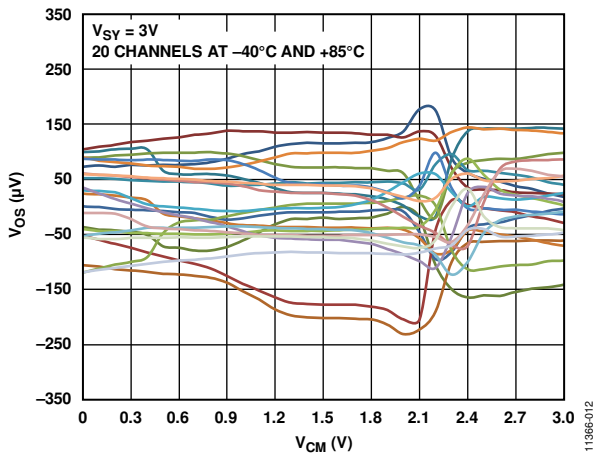


Figure 12. Input Offset Voltage vs. Common-Mode Voltage

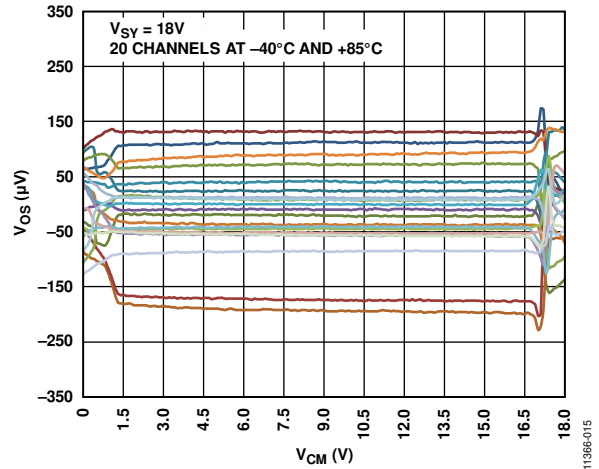


Figure 15. Input Offset Voltage vs. Common-Mode Voltage

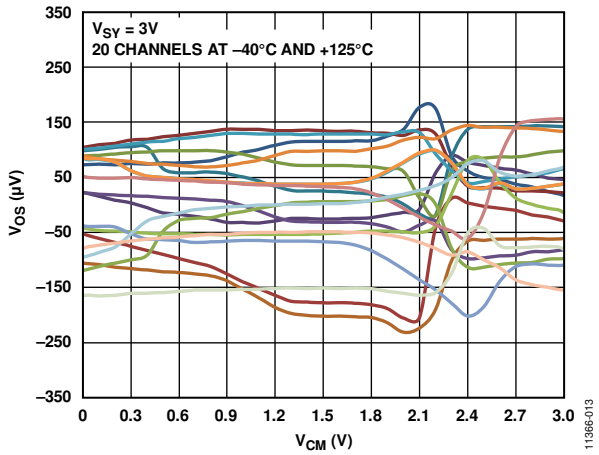


Figure 13. Input Offset Voltage vs. Common-Mode Voltage

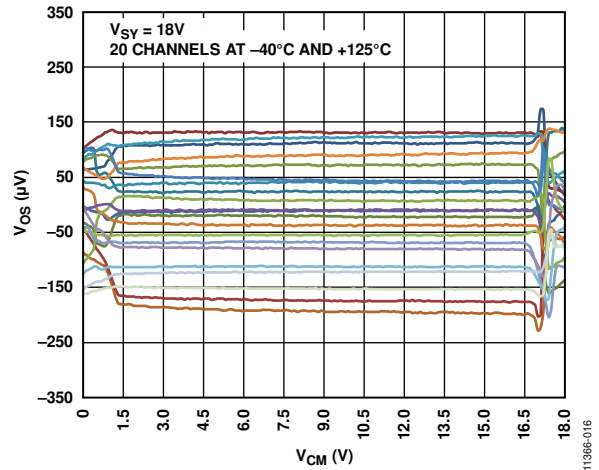


Figure 16. Input Offset Voltage vs. Common-Mode Voltage

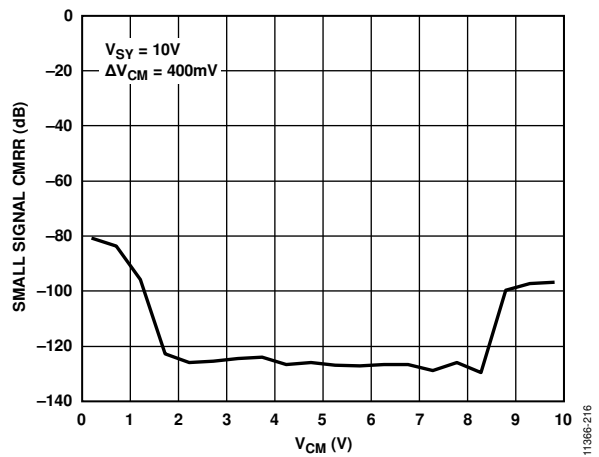


Figure 14. Small Signal CMRR vs. Common-Mode Voltage

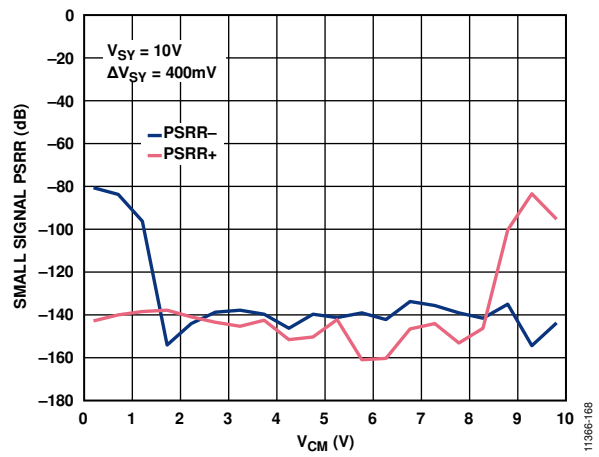


Figure 17. Small Signal PSRR vs. Common-Mode Voltage

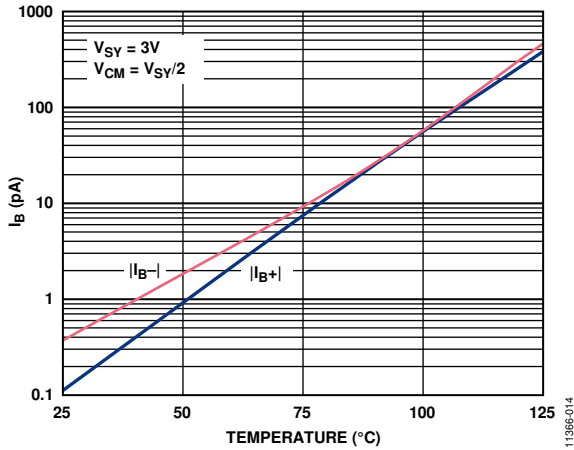


Figure 18. Input Bias Current vs. Temperature

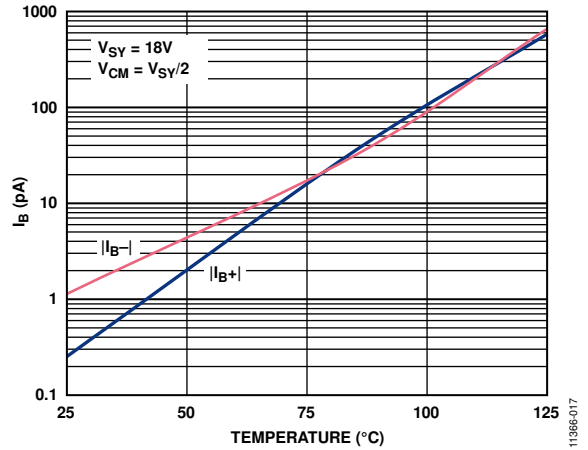


Figure 21. Input Bias Current vs. Temperature

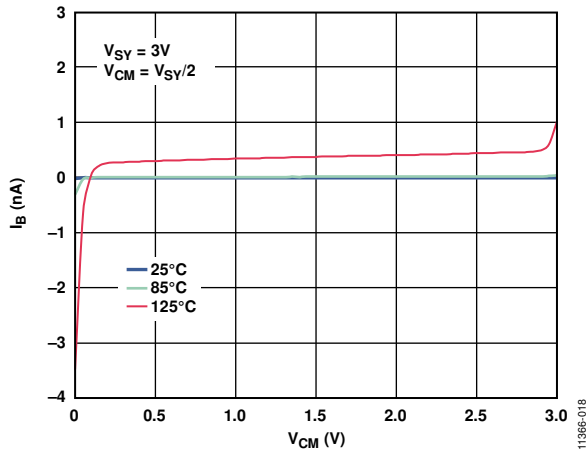


Figure 19. Input Bias Current vs. Common-Mode Voltage

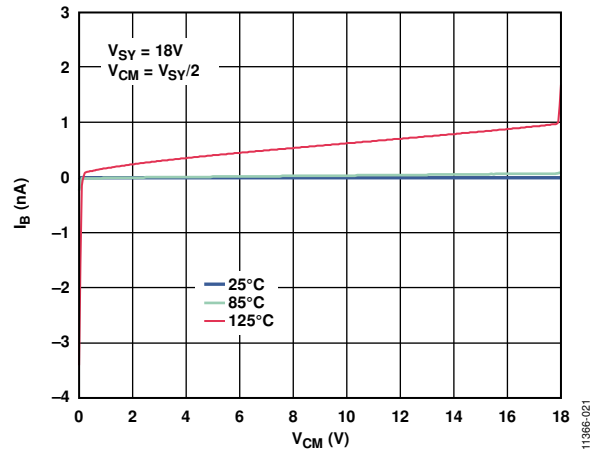


Figure 22. Input Bias Current vs. Common-Mode Voltage

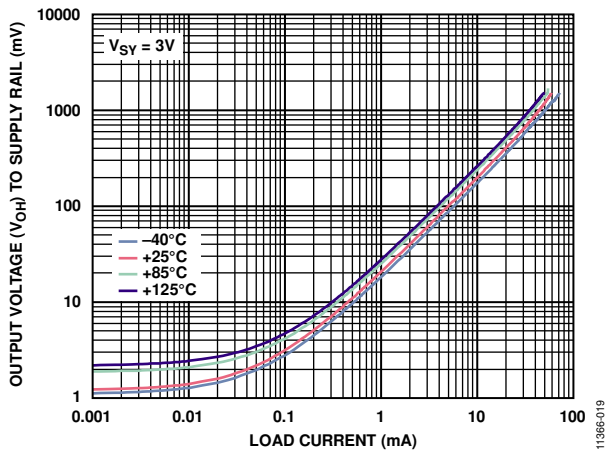


Figure 20. Output Voltage (V_{OH}) to Supply Rail vs. Load Current

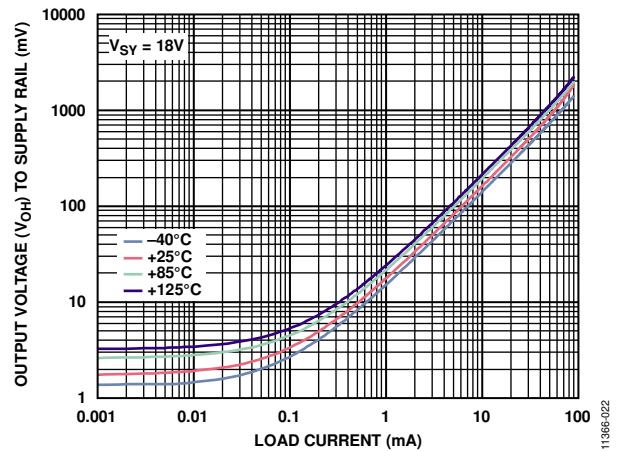


Figure 23. Output Voltage (V_{OH}) to Supply Rail vs. Load Current

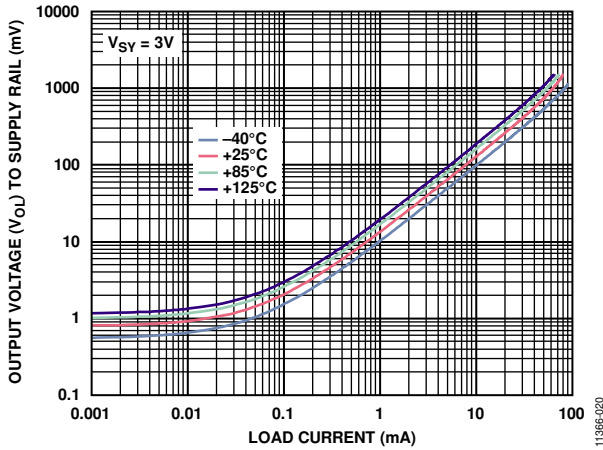


Figure 24. Output Voltage (V_{OL}) to Supply Rail vs. Load Current

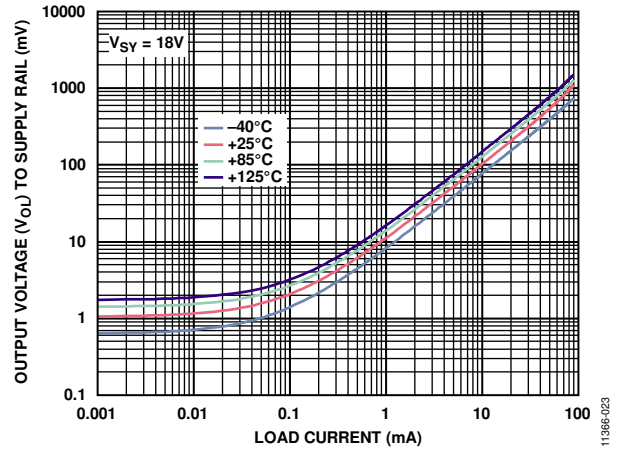


Figure 27. Output Voltage (V_{OL}) to Supply Rail vs. Load Current

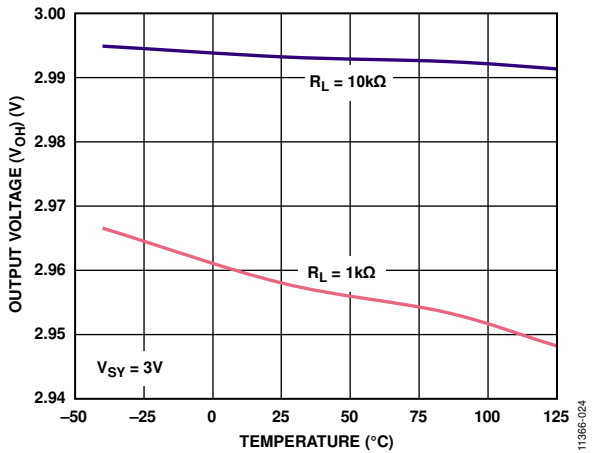


Figure 25. Output Voltage (V_{OH}) vs. Temperature

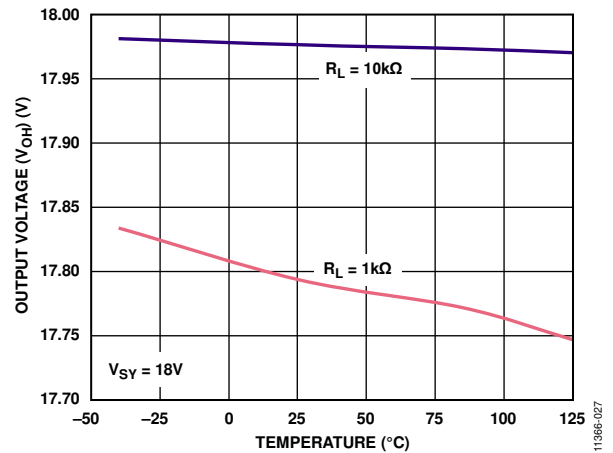


Figure 28. Output Voltage (V_{OH}) vs. Temperature

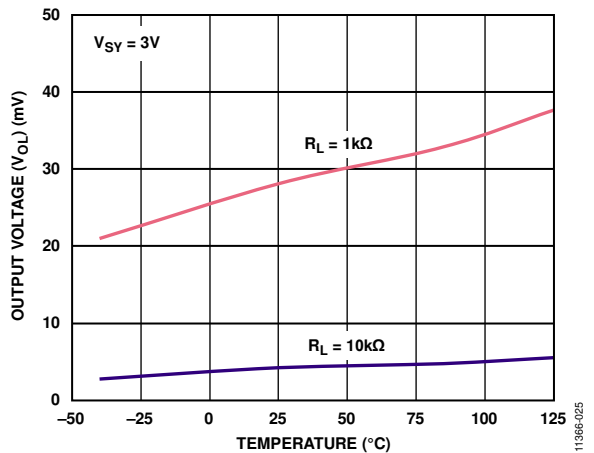


Figure 26. Output Voltage (V_{OL}) vs. Temperature

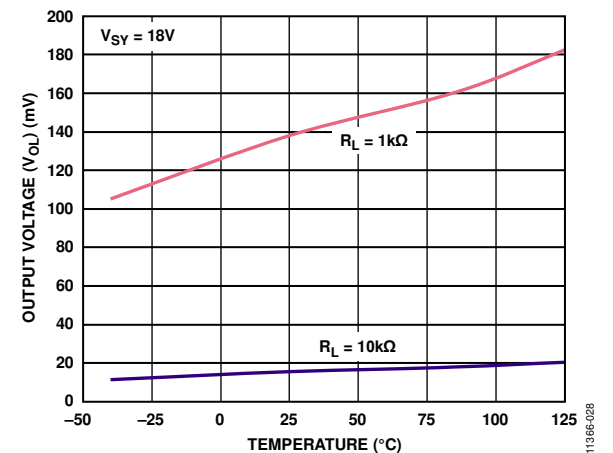


Figure 29. Output Voltage (V_{OL}) vs. Temperature

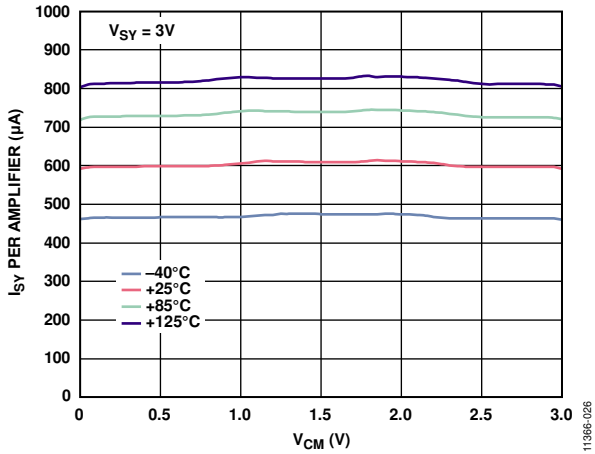


Figure 30. Supply Current vs. Common-Mode Voltage

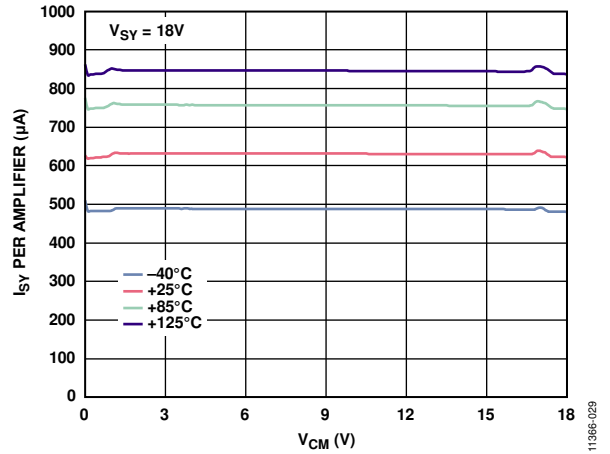


Figure 33. Supply Current vs. Common-Mode Voltage

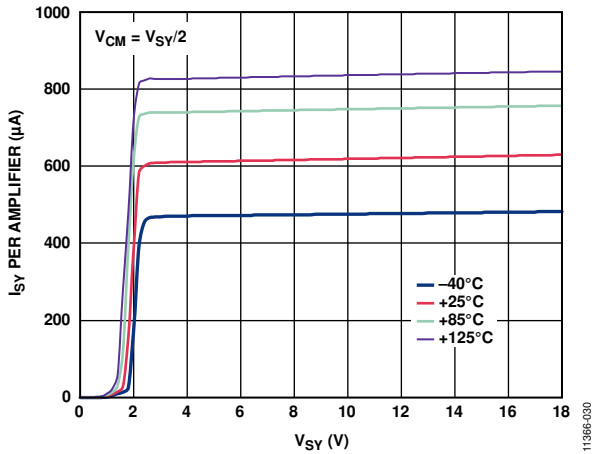


Figure 31. Supply Current vs. Supply Voltage

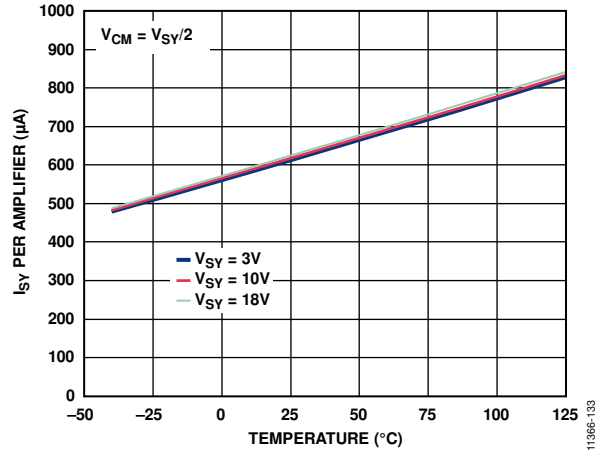


Figure 34. Supply Current vs. Temperature

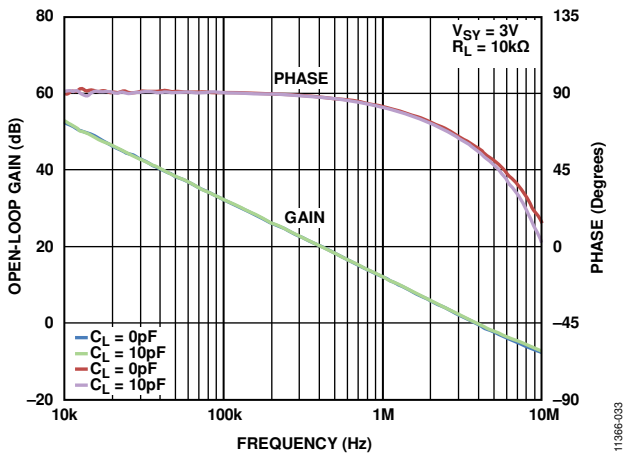


Figure 32. Open-Loop Gain and Phase vs. Frequency

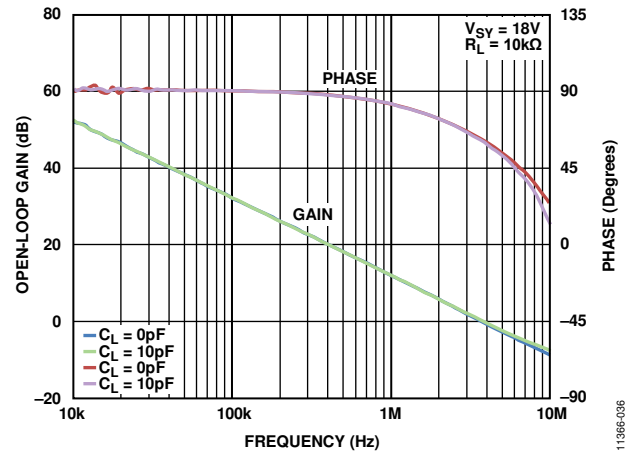


Figure 35. Open-Loop Gain and Phase vs. Frequency

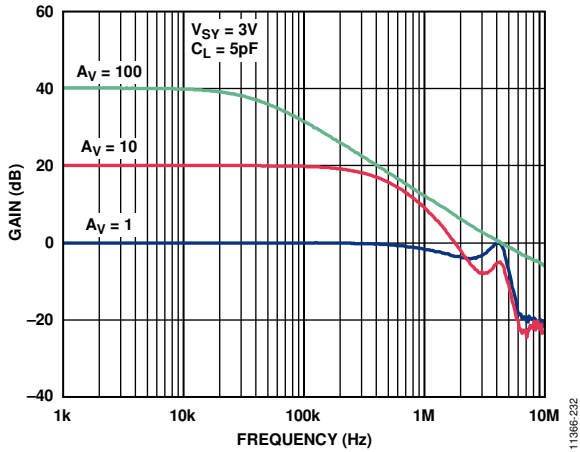


Figure 36. Closed-Loop Gain vs. Frequency

113866-232

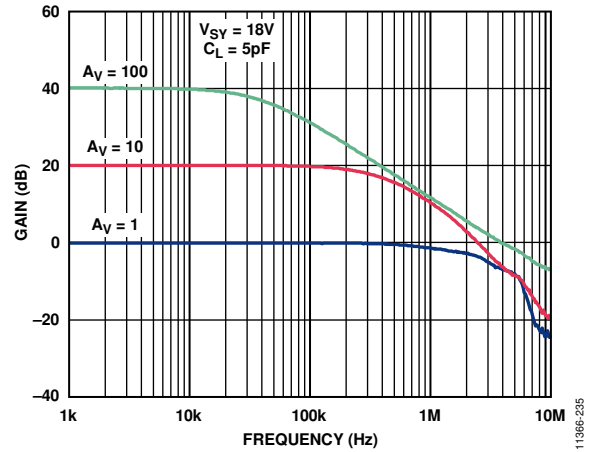


Figure 39. Closed-Loop Gain vs. Frequency

113866-235

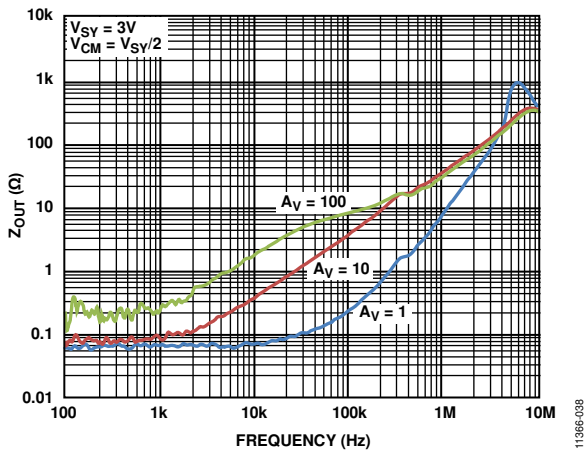


Figure 37. Output Impedance vs. Frequency

113866-038

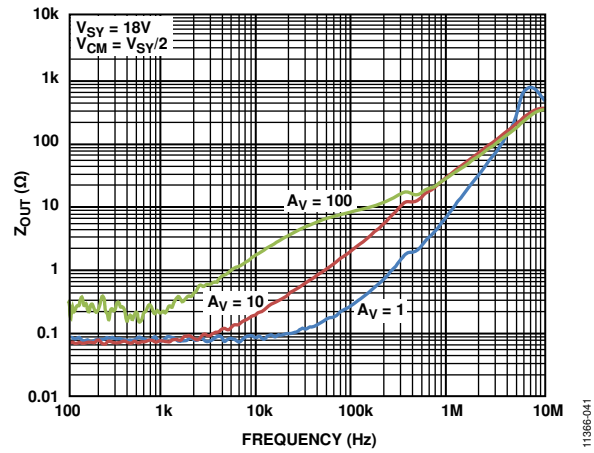


Figure 40. Output Impedance vs. Frequency

113866-041

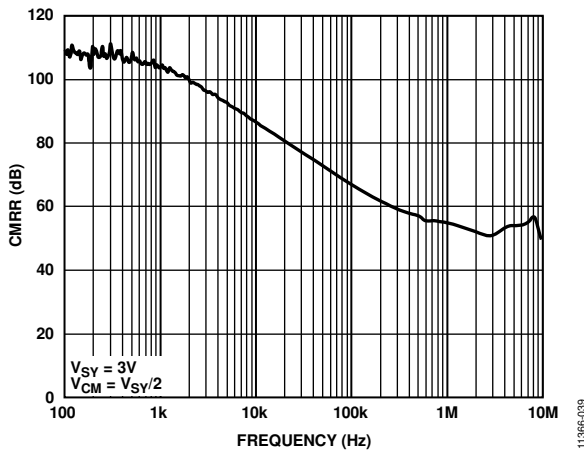


Figure 38. CMRR vs. Frequency

113866-039

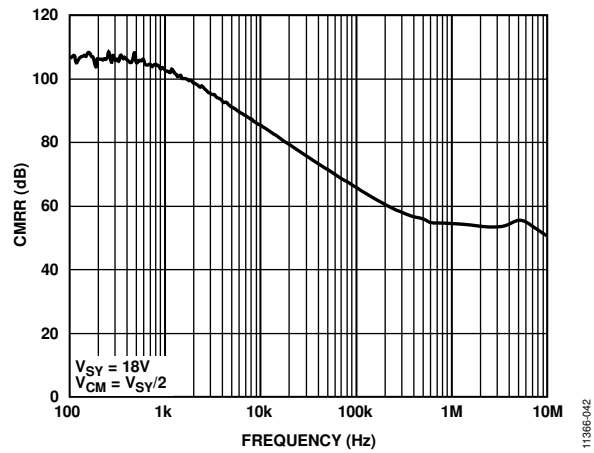


Figure 41. CMRR vs. Frequency

113866-042

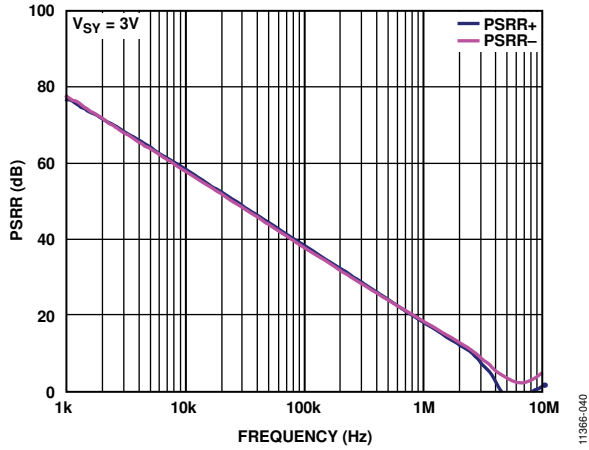


Figure 42. PSRR vs. Frequency

11386-040

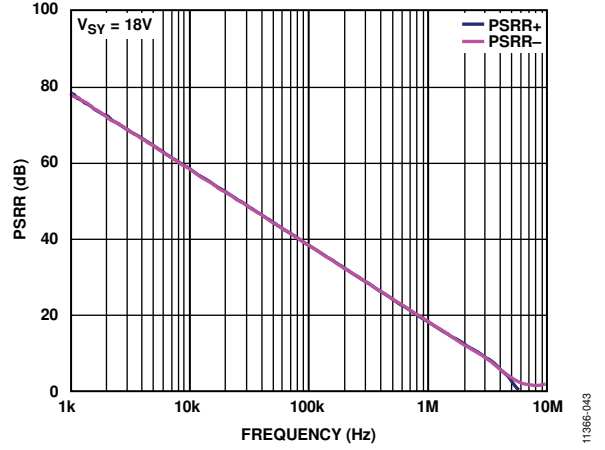


Figure 45. PSRR vs. Frequency

11386-043

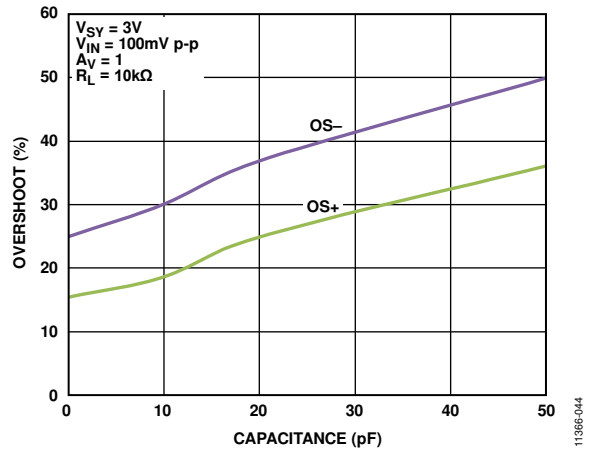


Figure 43. Small Signal Overshoot vs. Load Capacitance

11386-044

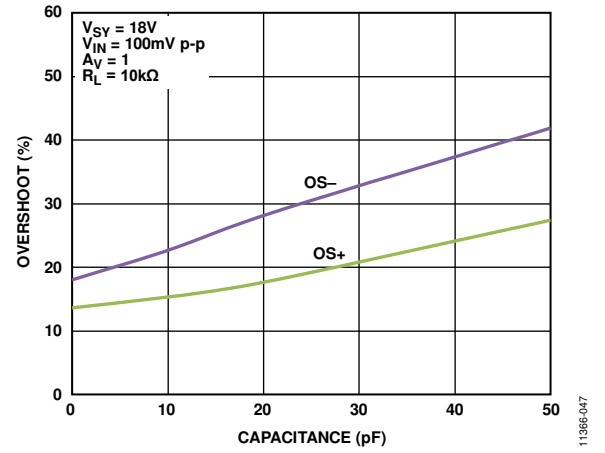


Figure 46. Small Signal Overshoot vs. Load Capacitance

11386-047

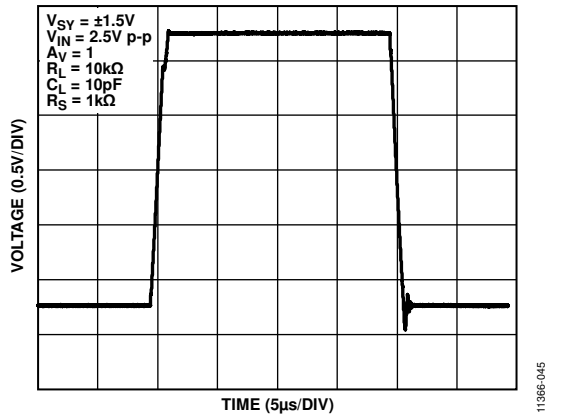


Figure 44. Large Signal Transient Response

11386-045

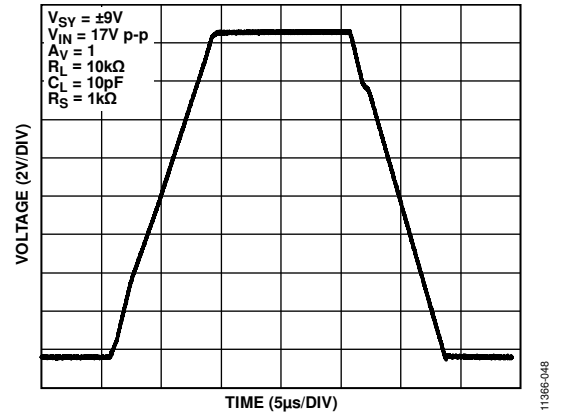


Figure 47. Large Signal Transient Response

11386-048

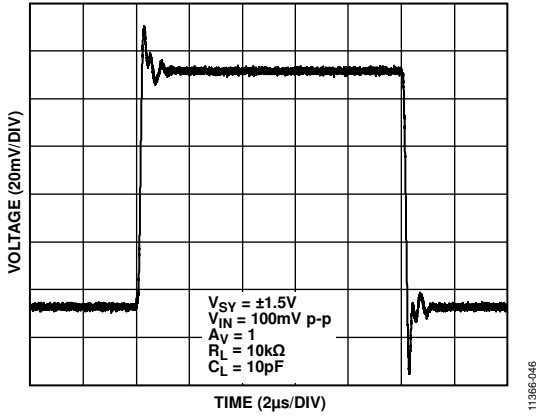


Figure 48. Small Signal Transient Response

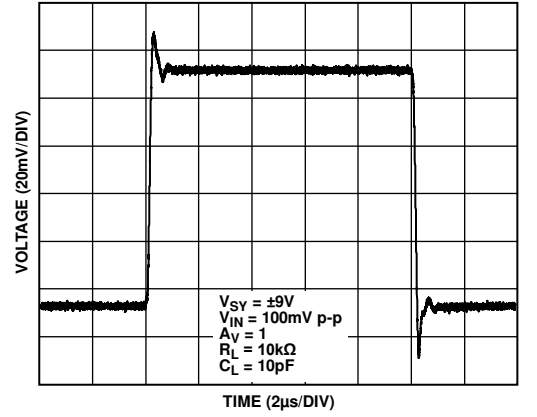


Figure 51. Small Signal Transient Response

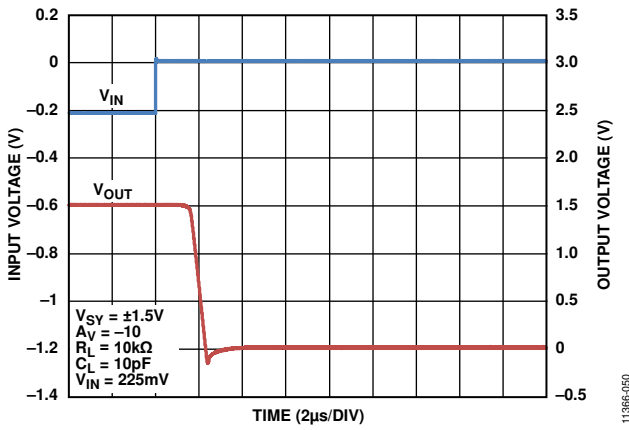


Figure 49. Positive Overload Recovery

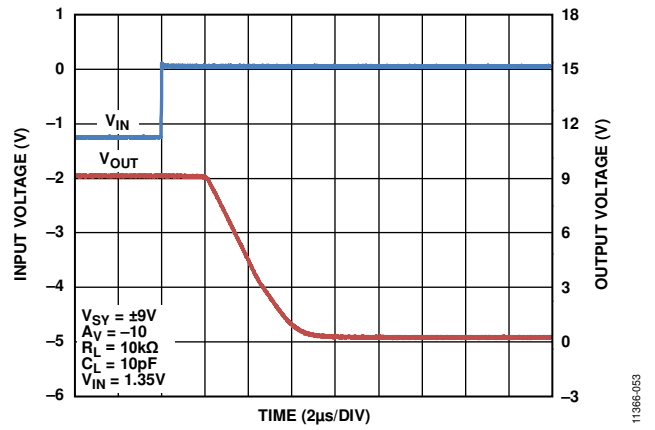


Figure 52. Positive Overload Recovery

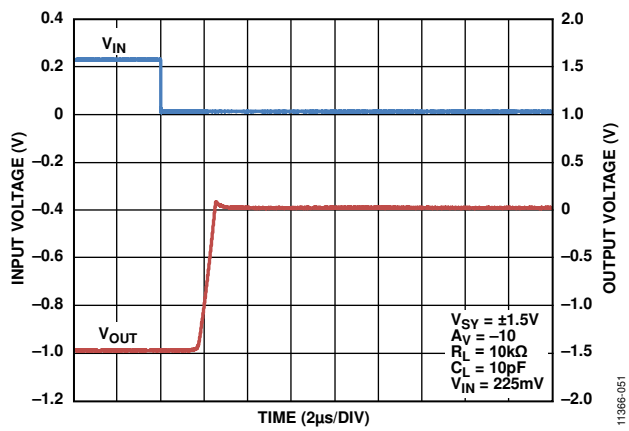


Figure 50. Negative Overload Recovery

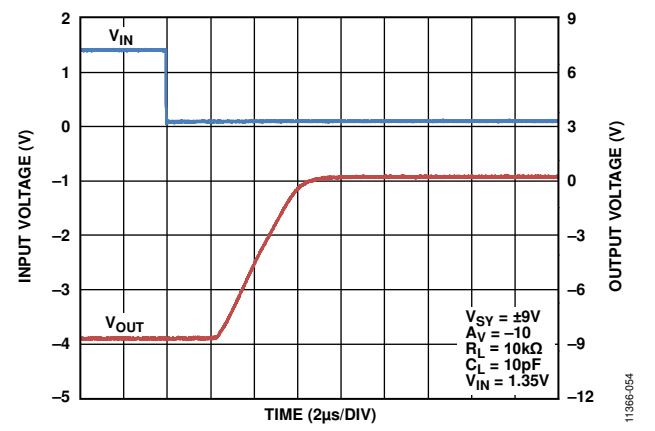


Figure 53. Negative Overload Recovery

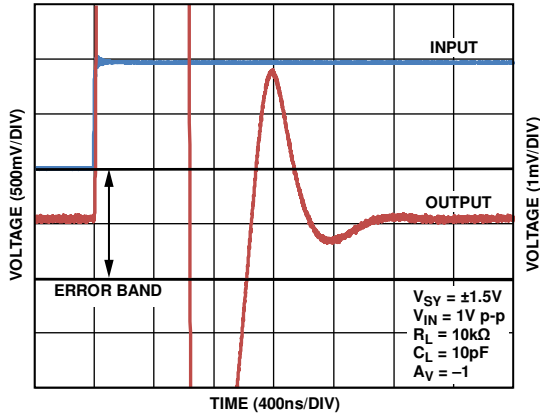


Figure 54. Positive Settling Time to 0.1%

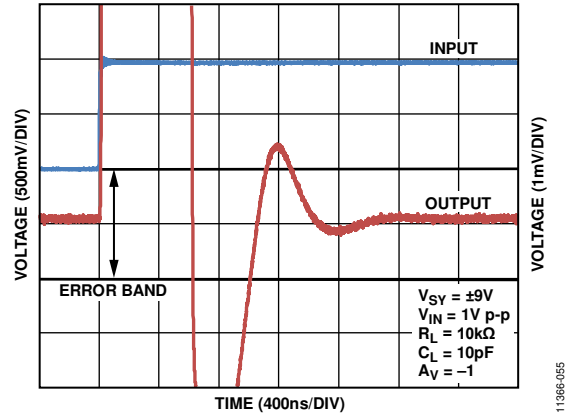


Figure 57. Positive Settling Time to 0.1%

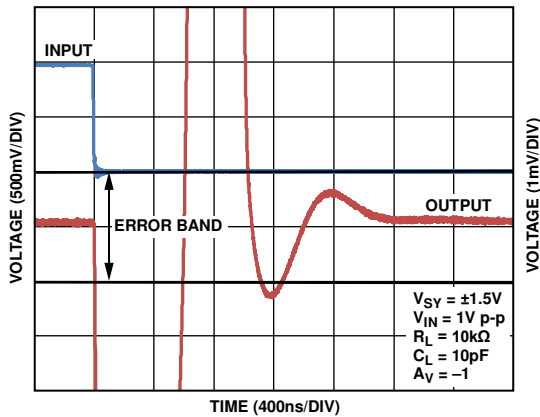


Figure 55. Negative Settling Time to 0.1%

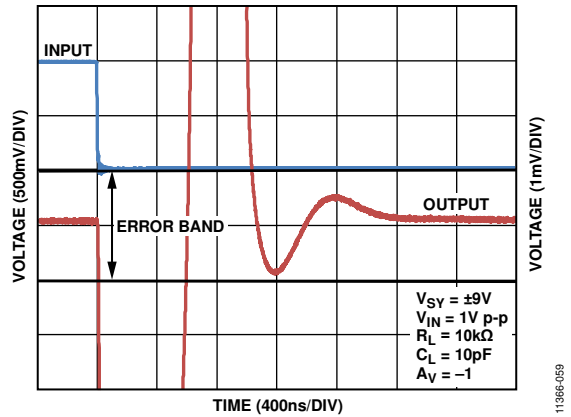


Figure 58. Negative Settling Time to 0.1%

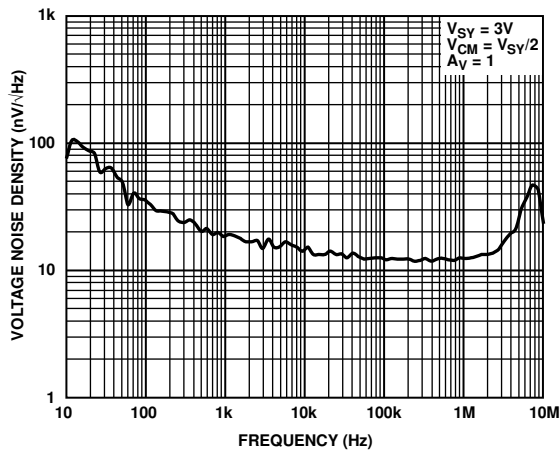


Figure 56. Voltage Noise Density vs. Frequency

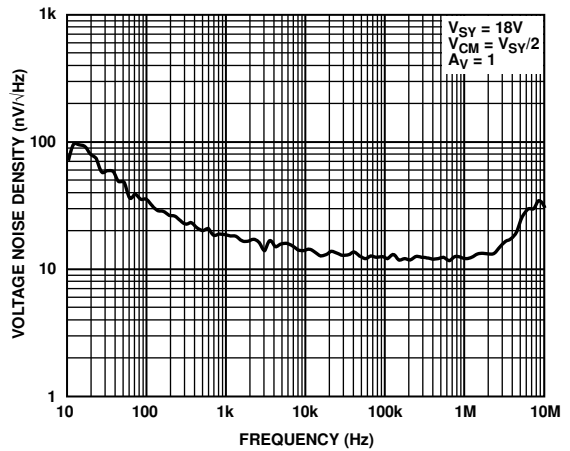


Figure 59. Voltage Noise Density vs. Frequency

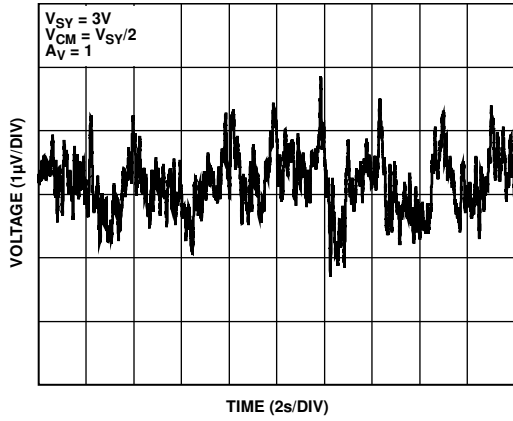


Figure 60. 0.1 Hz to 10 Hz Noise

11366-068

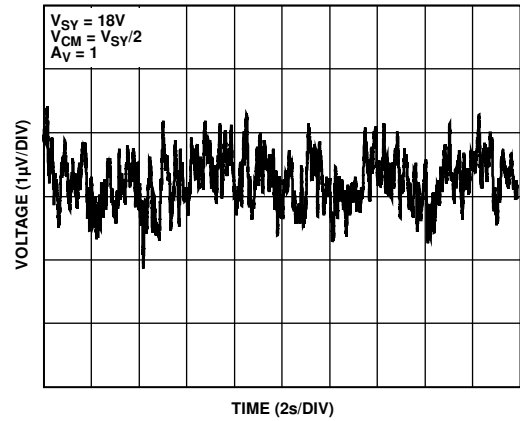


Figure 63. 0.1 Hz to 10 Hz Noise

11366-061

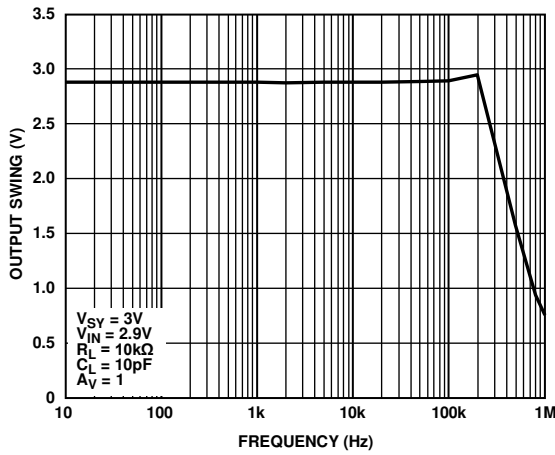


Figure 61. Output Swing vs. Frequency

11366-062

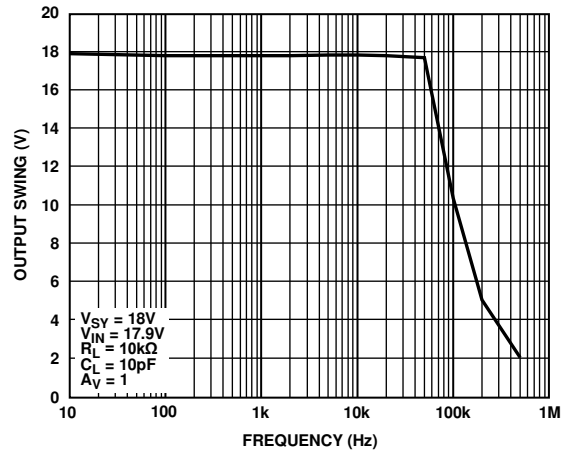


Figure 64. Output Swing vs. Frequency

11366-065

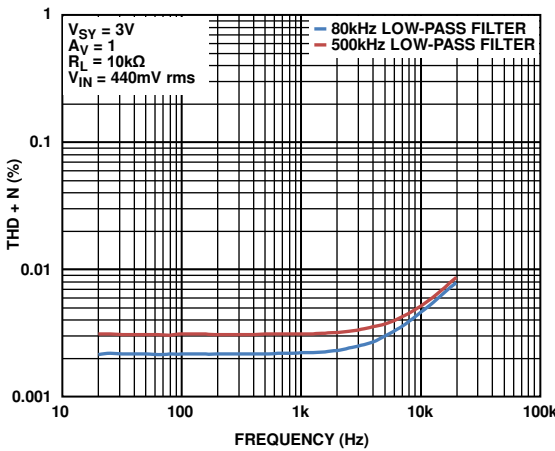


Figure 62. THD + N vs. Frequency

11366-063

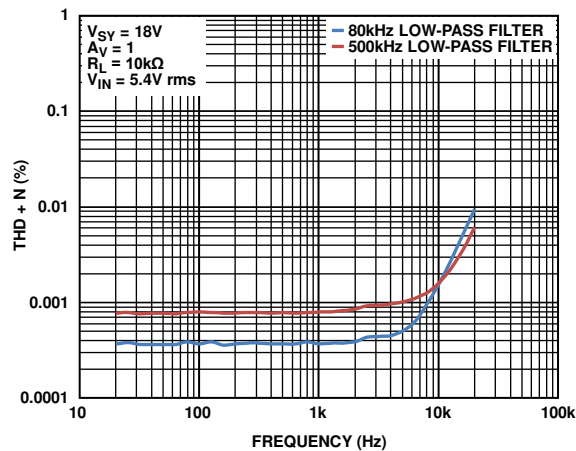


Figure 65. THD + N vs. Frequency

11366-066

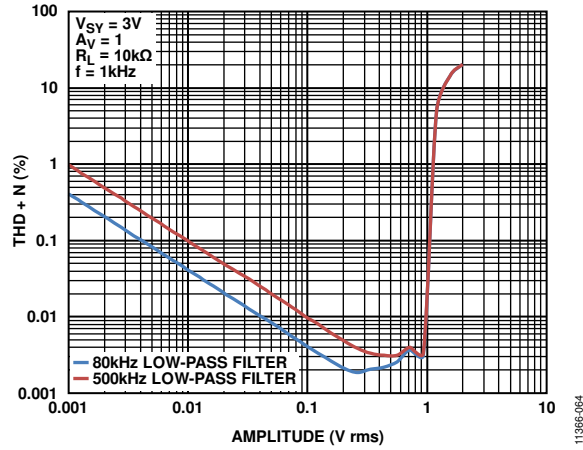


Figure 66. THD + N vs. Amplitude

11366-064

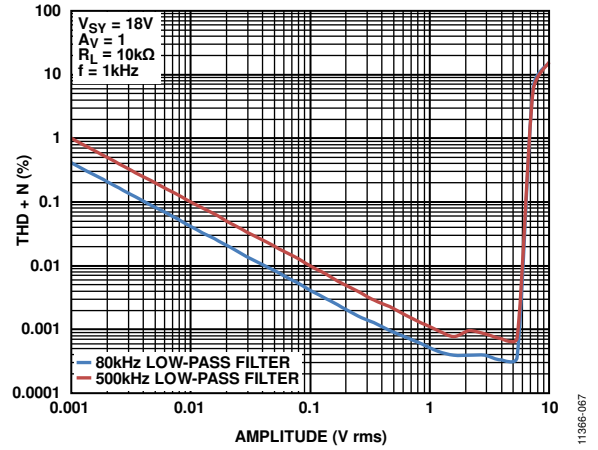


Figure 68. THD + N vs. Amplitude

11366-067

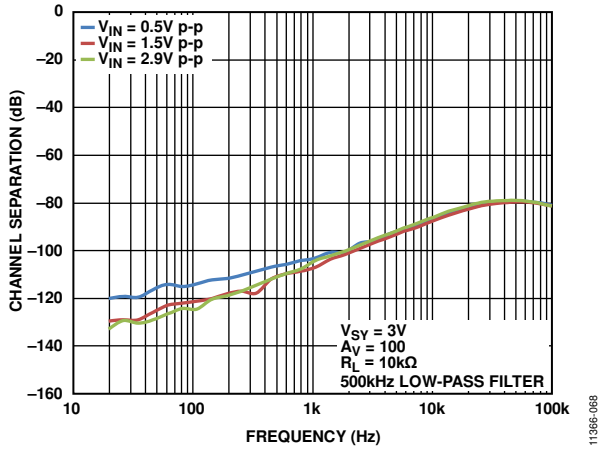


Figure 67. Channel Separation vs. Frequency

11366-068

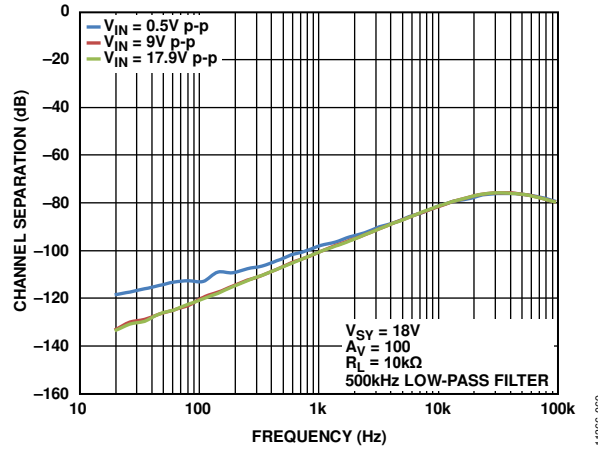


Figure 69. Channel Separation vs. Frequency

11366-069

APPLICATIONS INFORMATION

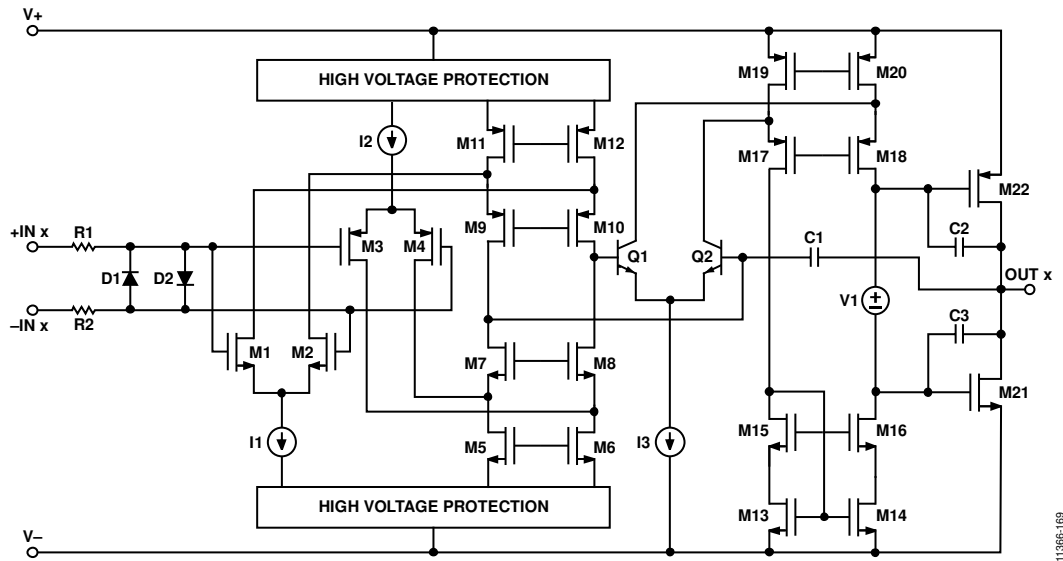


Figure 70. Simplified Schematic

The ADA4661-2 is a low power, rail-to-rail input and output, precision CMOS amplifier that operates over a wide supply voltage range of 3 V to 18 V. This amplifier uses the Analog Devices DigiTrim technique to achieve a higher degree of precision than is available from other CMOS amplifiers. The DigiTrim technique is a method of trimming the offset voltage of an amplifier after assembly. The advantage of postpackage trimming is that it corrects any offset voltages caused by mechanical stresses of assembly. To achieve a rail-to-rail input and output range with very low supply current, the ADA4661-2 uses unique input and output stages.

INPUT STAGE

Figure 70 shows the simplified schematic of the ADA4661-2. The amplifier uses a three-stage architecture with a fully differential input stage to achieve excellent dc performance specifications.

The input stage comprises two differential transistor pairs—a NMOS pair (M1, M2) and a PMOS pair (M3, M4)—and folded-cascode transistors (M5 to M12). The input common-mode voltage determines which differential pair is active. The PMOS differential pair is active for most of the input common-mode range. The NMOS pair is required for input voltages up to and including the upper supply rail. This topology allows the amplifier to maintain a wide dynamic input voltage range and maximize signal swing to both supply rails.

The proprietary high voltage protection circuitry in the ADA4661-2 minimizes the common-mode voltage changes seen by the amplifier input stage for most of the input common-mode range. This results in the amplifier having excellent disturbance rejection when operating in this preferred common-mode range. The performance benefits of operating within this preferred range are shown in the PSRR vs. V_{CM} (see Figure 17), CMRR vs. V_{CM} (see Figure 14), and V_{OS} vs. V_{CM}

graphs (see Figure 8, Figure 11, Figure 12, Figure 13, Figure 15, and Figure 16). The CMRR performance benefits of the reduced common-mode range are guaranteed at final test and shown in the electrical characteristics (see Table 2 to Table 4).

For most of the input common-mode voltage range, the PMOS differential pair is active. When the input common-mode voltage is within a few volts of the power supplies, the input transistors are exposed to these voltage changes. As the common-mode voltage approaches the positive power supply, the active differential pair changes from the PMOS pair to the NMOS pair. Differential pairs commonly exhibit different offset voltages. The handoff of control from one differential pair to the other creates a step like characteristic that is visible in the V_{OS} vs. V_{CM} graphs (see Figure 8, Figure 11, Figure 12, Figure 13, Figure 15, and Figure 16). This characteristic is inherent in all rail-to-rail input amplifiers that use the dual differential pair topology.

Additional steps in the V_{OS} vs. V_{CM} graphs are visible as the common-mode voltage approaches the negative power supply. These changes are a result of the load transistors (M5, M6) running out of headroom. As the load transistors are forced into the triode region of operation, the mismatch of their drain impedance becomes a significant portion of the amplifier offset. This effect can also be seen in the V_{OS} vs. V_{CM} graphs (see Figure 8, Figure 11, Figure 12, Figure 13, Figure 15, and Figure 16).

Current Source I2 drives the PMOS transistor pair. As the input common-mode voltage approaches the upper power supply, this current is reduced to zero. At the same time, a replica current source, I1, is increased from zero to enable the NMOS transistor pair.

The ADA4661-2 achieves its high performance specifications by using low voltage MOS devices for its differential inputs. These low voltage MOS devices offer excellent noise and bandwidth per unit of current. The input stage is isolated from the high

system voltages with proprietary protection circuitry. This regulation circuitry protects the input devices from the high supply voltages at which the amplifier can operate.

The input devices are also protected from large differential input voltages by clamp diodes (D1 and D2). These diodes are buffered from the inputs with two 120 Ω resistors (R1 and R2). The diodes conduct significant current whenever the differential voltage exceeds approximately 600 mV; in this condition, the differential input resistance falls to 240 Ω. It is possible for a significant amount of current to flow through these protection diodes. The user must ensure that current flowing into the input pins is limited to the absolute maximum of 10 mA.

GAIN STAGE

The second stage of the amplifier is composed of an NPN differential pair (Q1, Q2) and folded-cascode transistors (M13 to M20). The amplifier features nested Miller compensation (C1 to C3).

OUTPUT STAGE

The ADA4661-2 features a complementary output stage consisting of the M21 and M22 transistors. These transistors are configured in a Class AB topology and are biased by the voltage source, V1. This topology allows the output voltage to go within millivolts of the supply rails, achieving a rail-to-rail output swing. The output voltage is limited by the output impedance of the transistors, which are low R_{ON} MOS devices. The output voltage swing is a function of the load current and can be estimated using the output voltage to supply rail vs. load current graphs (see Figure 20, Figure 23, Figure 24, and Figure 27). The high voltage and high current capability of the ADA4661-2 output stage requires the user to ensure that it operates within the thermal safe operating area (see the Maximum Power Dissipation section).

MAXIMUM POWER DISSIPATION

The ADA4661-2 is capable of driving an output current up to 220 mA. However, the usable output load current drive is limited to the maximum power dissipation allowed by the device package. The absolute maximum junction temperature for the ADA4661-2 is 150°C (see Table 5). The junction temperature can be estimated as follows:

$$T_J = P_D \times \theta_{JA} + T_A$$

The power dissipated in the package (P_D) is the sum of the quiescent power dissipation and the power dissipated by the output stage transistor. It can be calculated as follows:

$$P_D = (V_{SY} \times I_{SY}) + (V_{SY} - V_{OUT}) \times I_{LOAD}$$

where:

V_{SY} is the power supply rail.

I_{SY} is the quiescent current.

V_{OUT} is the output of the amplifier.

I_{LOAD} is the output load.

Do not exceed the maximum junction temperature for the device, 150°C. Exceeding the junction temperature limit can cause degradation in the parametric performance or even

destroy the device. To ensure proper operation, it is necessary to observe the maximum power derating curves. Figure 71 shows the maximum safe power dissipation in the package vs. the ambient temperature on a standard 4-layer JEDEC board. The exposed pad of the LFCSP package is soldered to the board.

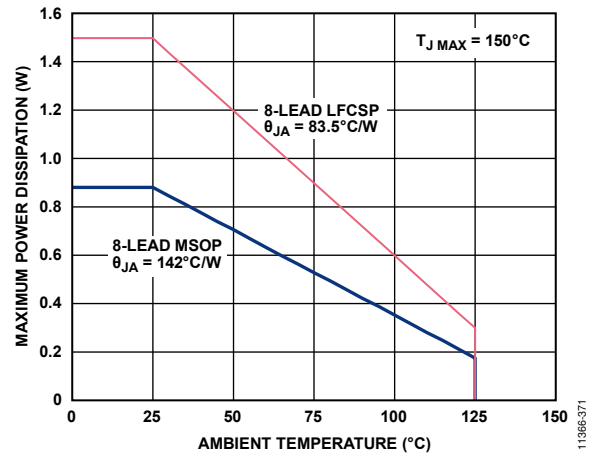


Figure 71. Maximum Power Dissipation vs. Ambient Temperature

Refer to [Technical Article MS-2251, Data Sheet Intricacies—Absolute Maximum Ratings and Thermal Resistances](#), for more information.

RAIL-TO-RAIL INPUT AND OUTPUT

The ADA4661-2 features rail-to-rail input and output with a supply voltage from 3 V to 18 V. Figure 72 shows the input and output waveforms of the ADA4661-2 configured as a unity-gain buffer with a supply voltage of ±9 V. With an input voltage of ±9 V, the ADA4661-2 allows the output to swing very close to both rails. Additionally, it does not exhibit phase reversal.

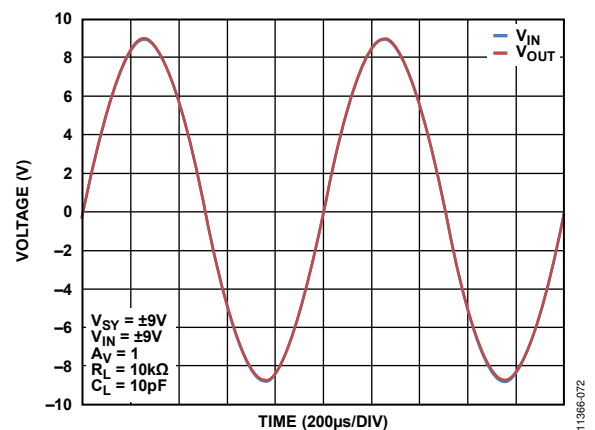


Figure 72. Rail-to-Rail Input and Output

COMPARATOR OPERATION

An op amp is designed to operate in a closed-loop configuration with feedback from its output to its inverting input. Figure 73 shows the ADA4661-2 configured as a voltage follower with an input voltage that is always kept at the midpoint of the power supplies. The same configuration is applied to the unused channel. A1 and A2 indicate the placement of ammeters to measure supply current. I_{SY+} refers to the current flowing from the upper supply rail to the op amp, and I_{SY-} refers to the current flowing from the op amp to the lower supply rail. As shown in Figure 74, in normal operating conditions, the total current flowing into the op amp is equivalent to the total current flowing out of the op amp, where $I_{SY+} = I_{SY-} = 630 \mu\text{A}$ per amplifier at $V_{SY} = 18 \text{ V}$.

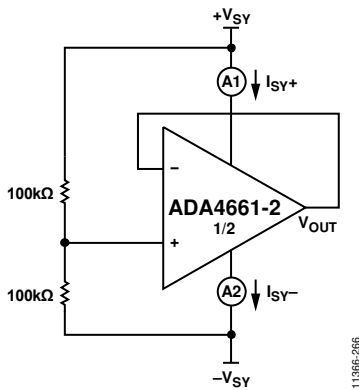


Figure 73. Voltage Follower

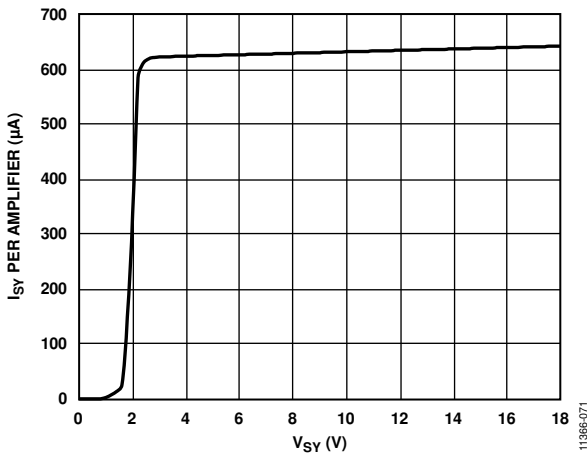


Figure 74. Supply Current vs. Supply Voltage (Voltage Follower)

In contrast to op amps, comparators are designed to work in an open-loop configuration and to drive logic circuits. Although op amps are different from comparators, occasionally an unused section of a dual op amp is used as a comparator to save board space and cost; however, this is not recommended for the ADA4661-2.

Figure 75 and Figure 76 show the ADA4661-2 configured as a comparator, with 100 kΩ resistors in series with the input pins. Any unused channels are configured as buffers with the input voltage kept at the midpoint of the power supplies.

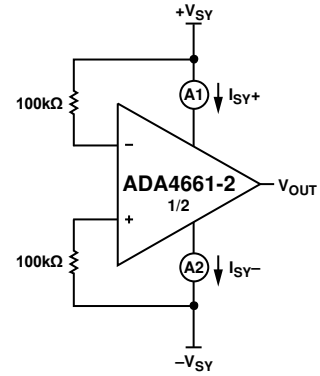


Figure 75. Comparator A

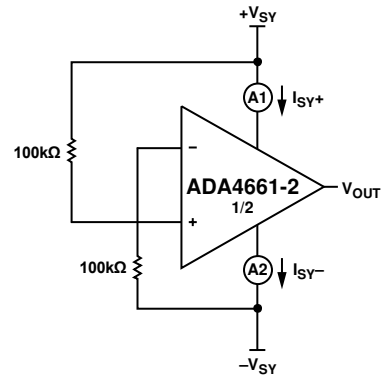


Figure 76. Comparator B

Figure 77 shows the supply currents for both comparator configurations. In comparator mode, the ADA4661-2 does not power up completely. For more information about configuring using on op amps as comparators, see the AN-849 Application Note, *Using Op Amps as Comparators*.

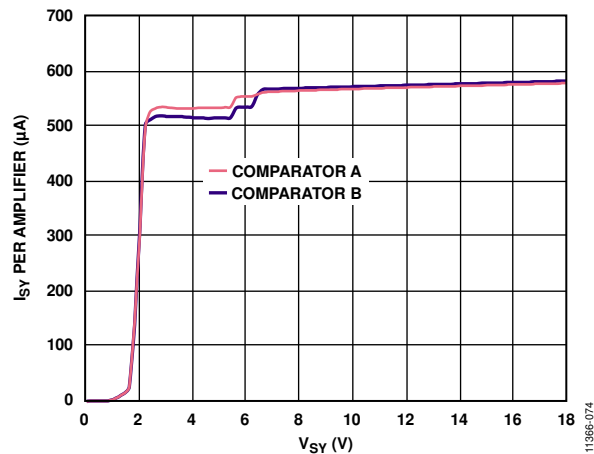


Figure 77. Supply Current vs. Supply Voltage (ADA4661-2 as a Comparator)